Ordering number : EN*5793

CMOS IC

LC378000RP

Internally Synchronized Silicon Gate 8M (1,048,576-word × 8-bit, 524,288-word × 16-bit) Mask ROM

Preliminary

Overview

The LC378000RP is an 8-Mbit mask ROM that can be switched between byte mode, which provides an 8-bit × 1,048,576-word structure, and word mode, which provides a 16-bit × 524,288-word structure. Since this device operates over the wide supply voltage range of 2.6 to 5.5 V and achieves access times (t_{AA}) of 100 ns (at V_{CC} = 4.5 to 5.5 V) and 200 ns (at V_{CC} = 2.6 to 5.5 V), it can be used in a wide range of systems, from 5-V systems requiring high-speed access to 3-V battery operated systems.

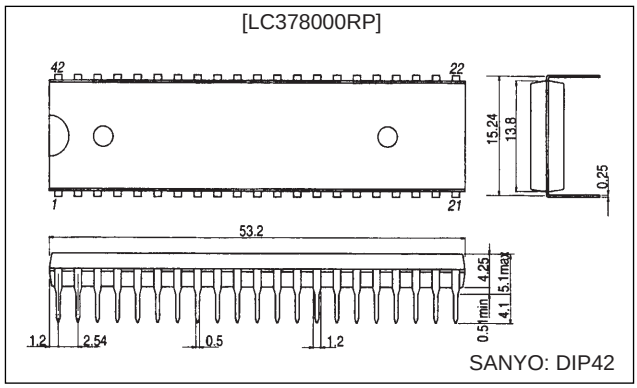
Features

- Supply voltage range: 2.6 to 5.5 V
- Access time (t_{AA}): 100 ns (V_{CC} = 4.5 to 5.5 V)
  (t_{CA}): 110 ns (V_{CC} = 4.5 to 5.5 V)
  200 ns (V_{CC} = 2.6 to 5.5 V)
- Switchable between 8-bit and 16-bit data path widths
  Byte mode: 1,048,576 words × 8 bits
  Word mode: 524,288 words × 16 bits
- Operating current drain: 90 mA (maximum)
- Standby current: 30 µA (maximum)
- Fully static operation (internal synchronization)
- Three-state outputs
- Package: 42-pin DIP (600 mil) plastic package

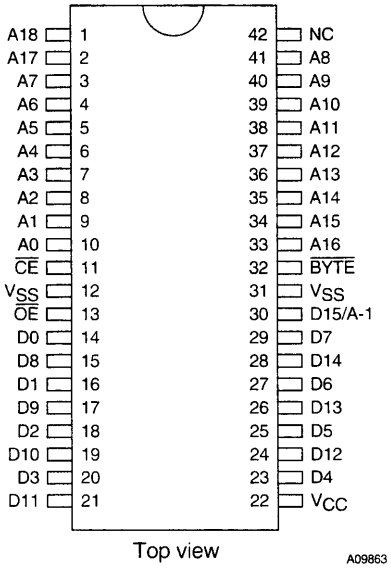
Package Dimensions

unit: mm

3014A-DIP42



Pin Assignment

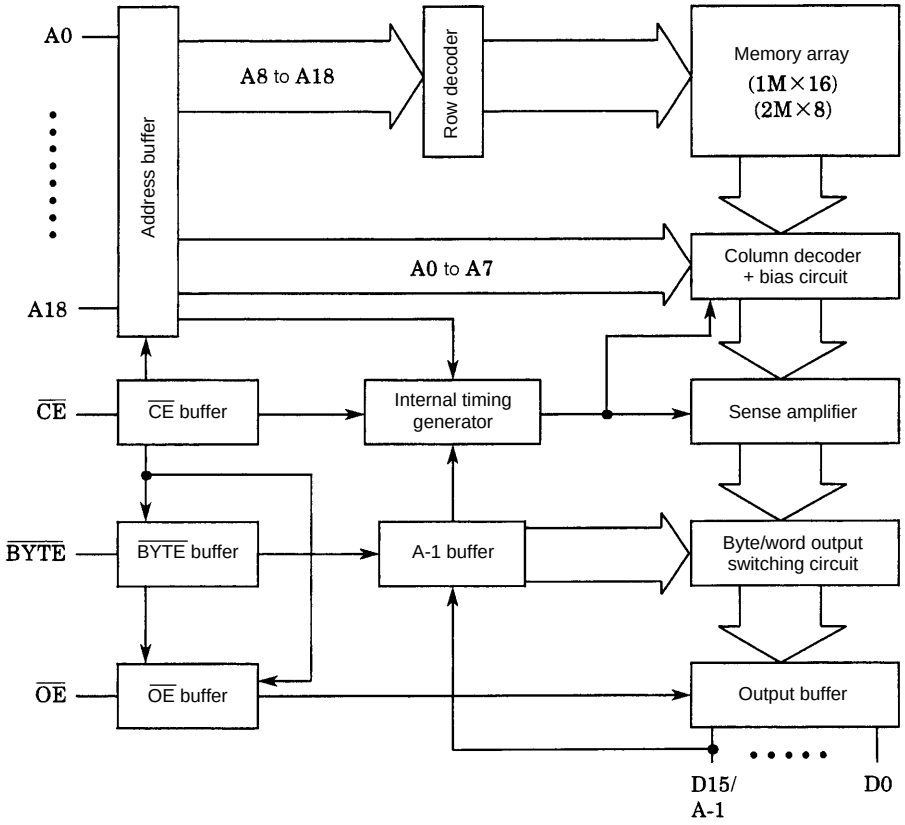


Pin Functions

A0 to A19	Address inputs
D0 to D15/A-1	Data outputs
$\overline{CE}$	Chip enable input
$\overline{OE}$	Output enable input
$\overline{BYTE}$	Byte/word mode switching
V_{CC}	Power
V_{SS}	Ground

D15/A-1: In byte mode, this pin functions as the A-1 address input, and in word mode, it functions as the D15 data output pin.

Block Diagram



Function Logic Table

$\overline{CE}$	$\overline{OE}$	$\overline{BYTE}$	Output pin state	Current drain
H	X	L	High impedance	Standby mode level
L	H	L	High impedance	Operating mode level
L	L	L	DOUT × 8 (BYTE MODE)*	Operating mode level
H	X	H	High impedance	Standby mode level
L	H	H	High impedance	Operating mode level
L	L	H	DOUT × 16 (WORD MODE)	Operating mode level

Note: X: A high-level or low-level input
D8 to 14 are high impedance and D15 functions as the A-1 address input.

Specifications

Absolute Maximum Ratings*

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage	V_{CC}		–0.3 to +7.0	V
Input pin voltage	V_{IN}		–0.3* to V_{CC} + 0.3	V
Output pin voltage	V_{OUT}		–0.3 to V_{CC} + 0.3	V
Allowable power dissipation	Pd max	Ta = 25°C	1.0	W
Operating temperature	Topr		–10 to +70	°C
Storage temperature	Tstg		–55 to +125	°C

Note: Application of stresses greater than or equal to the maximum ratings may lead to device destruction.
*: Minimum value minus 3.0 V for pulses with widths of 30 ns or less.

Capacitance Characteristics* at Ta = 25°C, f = 1.0 MHz

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input pin capacitance	C_{IN}	V_{IN} = 0 V. Reference value using the Sanyo DIP.			8	pF
Output pin capacitance	C_{OUT}	V_{OUT} = 0 V. Reference value using the Sanyo DIP.			10	pF

Note: These parameters are not tested in all units, but rather are sampled in a subset of units produced.

DC Allowable Operating Ranges at Ta = –10 to +70°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Supply voltage	V_{CC} max		2.6	5.0	5.5	V
Input high-level voltage	V_{IH}		2.2		V_{CC} + 0.3	V
Input low-level voltage	V_{IL}		–0.3		0.6	V

DC Electrical Characteristics at Ta = –10 to +70°C, V_{CC} = 2.6 to 5.5 V

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Operating current drain	I_{CCA1}	$\overline{CE}$ = 0.2 V, V_I = V_{CC} – 0.2 V/0.2 V			30	mA
	I_{CCA2}	$\overline{CE}$ = V_{IL}, I_O = 0 mA, V_I = V_{IH}/V_{IL}, f = 10 MHz			90	mA
Standby current drain	I_{CCS1}	$\overline{CE}$ = V_{CC} – 0.2 V			30 (1.0)	µA
	I_{CCS2}	$\overline{CE}$ = V_{IH}			1.0 (0.3)	mA
Input leakage current	I_{LI}	V_{IN} = 0 to V_{CC}			±1.0	µA
Output leakage current	I_{LO}	$\overline{CE}$ or $\overline{OE}$ = V_{IH}, V_{OUT} = 0 to V_{CC}			±1.0	µA
Output high-level voltage	V_{OH}	I_{OH} = –0.5 mA	0.8 V_{CC}			V
Output low-level voltage	V_{OL}	I_{OL} = 0.5 mA			0.2	V

Note: Values in parentheses are guaranteed at Ta = 25°C.

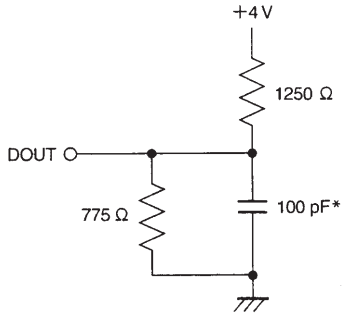
AC Characteristics at Ta = –10 to +70°C, V_{CC} = 2.6 to 5.5 V

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Cycle time	t_{CYC}		200 (100)			ns
Address access time	t_{AA}				200 (100)	ns
$\overline{CE}$ enable time	t_{CEON}		200 (135)			ns
$\overline{CE}$ access time	t_{CA}				200 (110)	ns
$\overline{OE}$ access time	t_{OA}				100 (40)	ns
Output hold time	t_{OH}		20			ns
Output disable time*	t_{OD}				100	ns

Note: t_{OD} is stipulated as the time from the rise of either $\overline{CE}$ or $\overline{OE}$ (whichever occurs first) to the point when the output goes to the high-impedance state.
These parameters are not tested in all units, but rather are sampled in a subset of units produced.
Values in parentheses are for V_{CC} = 4.5 to 5.5 V.

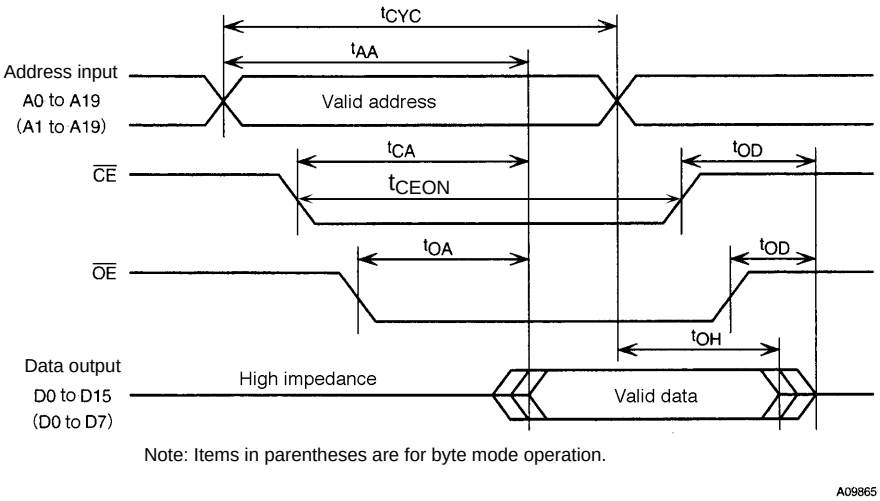
Test Conditions

Input voltage amplitude	0.4 V to 2.8 V
Rise and fall times	5 ns
Input discrimination level	1.5 V
Output discrimination level	1.5 V
Output load	See figure.



Output Load

Timing Waveforms



Note: Items in parentheses are for byte mode operation.

A09865

Notes on System Design

This IC adopts the ATD technique, in which operation starts when a change in either the CE or address inputs is detected. This means that the output data immediately after power is applied is invalid. When using this IC as program memory for the Z80 and similar microprocessors, applications must take into account the fact that valid data will not be output after power is first applied unless the value of either the CE line or at least one of the address lines is changed after the power supply has stabilized.

Another point due to the use of the ATD technique is that this IC is sensitive to input noise. Do not apply voltages outside the allowable DC input levels for extended periods and do not apply input voltages with large noise components.